

ZXMP3F30FH

30V SOT23 P-CHANNEL ENHANCEMENT MODE MOSFET

Summary

$V_{(BR)DSS}$ (V)	$R_{DS(on)}$ (Ω)	I_D (A)
-30	0.080 @ $V_{GS} = -10V$	-4.0
	0.140 @ $V_{GS} = -4.5V$	

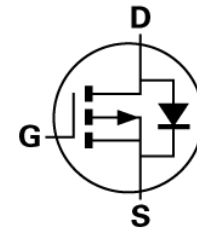


Description

This new generation Trench MOSFET from Zetex has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance.

Features

- Low on-resistance
- Fast switching speed
- 4.5V gate drive capability
- Thermally enhanced SOT23 package

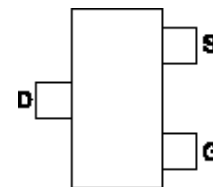


Applications

- Power management
- Portable Equipment
- Battery charging

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP3F30FHTA	7"	8mm	3,000



Pinout – top view

Device marking

KPA

Absolute Maximum Ratings

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-Source voltage	V_{DSS}	-30	V
Gate-Source voltage	V_{GS}	± 20	V
Continuous Drain current @ $V_{GS} = -10V$; $T_A = 25^\circ C$ ^(b) @ $V_{GS} = -10V$; $T_A = 70^\circ C$ ^(b) @ $V_{GS} = -10V$; $T_A = 25^\circ C$ ^(a) @ $V_{GS} = -10V$; $T_L = 25^\circ C$ ^(d)	I_D	-3.4 -2.7 -2.8 -4.0	V
Pulsed Drain current ^(c)	I_{DM}	-15.3	A
Continuous Source current (Body diode) ^(b)	I_S	-2	A
Pulsed Source current (Body diode) ^(c)	I_{SM}	-15.3	A
Power dissipation at $T_A = 25^\circ C$ ^(a) Linear derating factor	P_D	0.95 7.6	W mW/ $^\circ C$
Power dissipation at $T_A = 25^\circ C$ ^(b) Linear derating factor	P_D	1.4 11.2	W mW/ $^\circ C$
Power dissipation at $T_L = 25^\circ C$ ^(d) Linear derating factor	P_D	1.96 15.7	W mW/ $^\circ C$
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	$^\circ C$

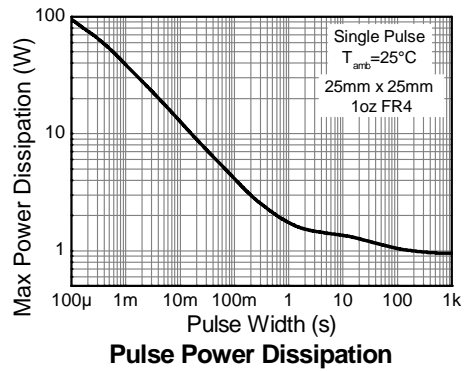
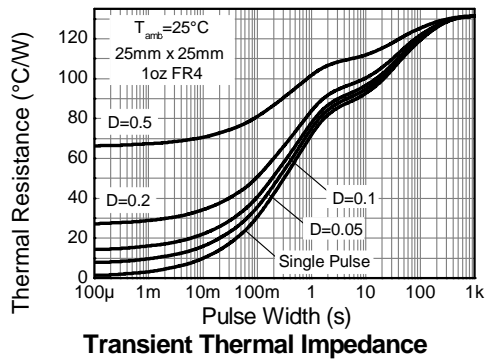
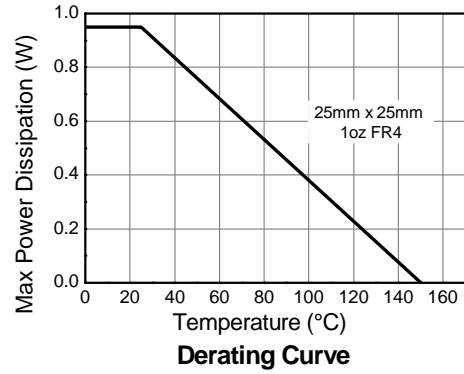
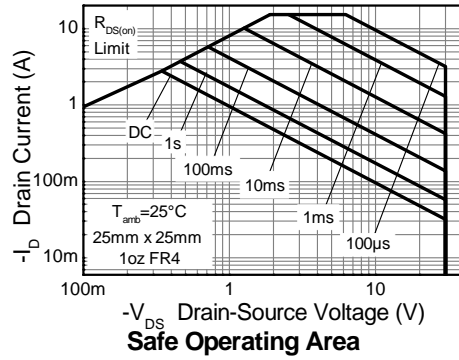
Thermal resistance

Parameter	Symbol	Value	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	131	$^\circ C/W$
Junction to ambient ^(b)	$R_{\theta JA}$	89	$^\circ C/W$
Junction to lead ^(d)	$R_{\theta JL}$	63.77	$^\circ C/W$

NOTES:

- (a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on FR4 PCB measured at $t \leq 10$ sec.
- (c) Repetitive rating on 25mm x 25mm FR4 PCB, $D=0.02$, pulse width 300us – pulse width limited by maximum junction temperature.
- (d) Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics



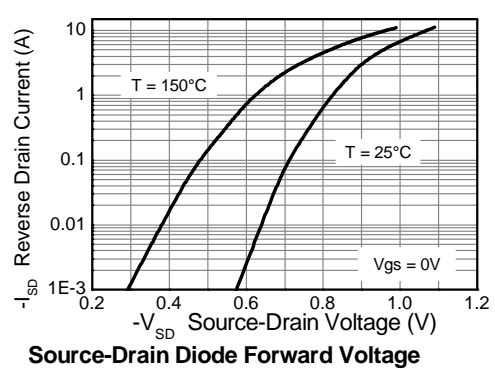
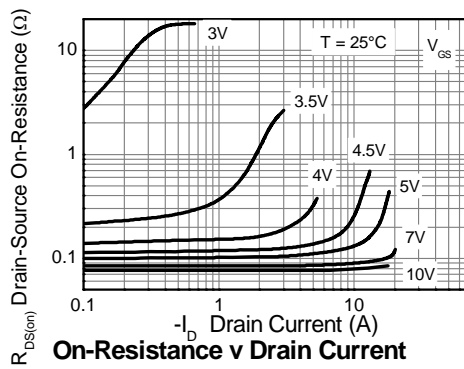
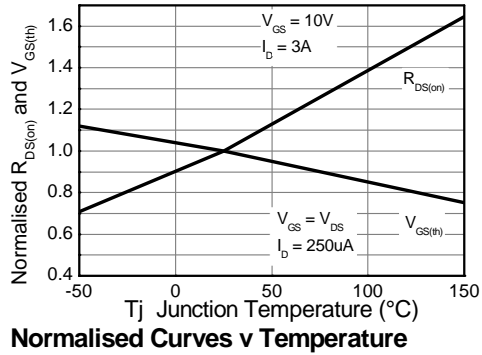
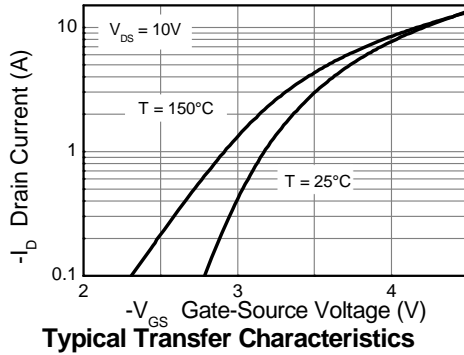
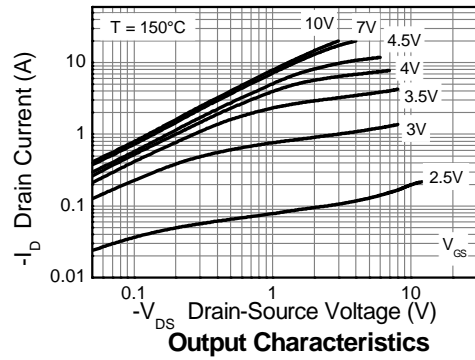
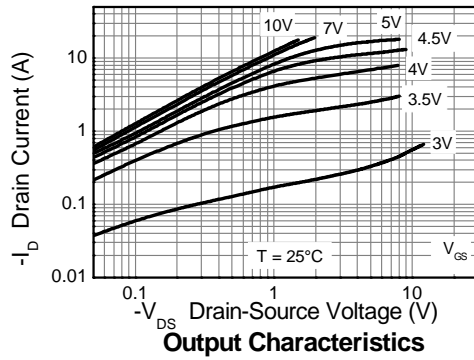
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-Source breakdown voltage	$V_{(BR)DSS}$	-30			V	$I_D = -250\mu\text{A}$, $V_{GS}=0\text{V}$
Zero Gate voltage Drain current	I_{DSS}			-1.0	μA	$V_{DS}=-30\text{V}$, $V_{GS}=0\text{V}$
Gate-Body leakage	I_{GSS}			100	nA	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$
Gate-Source threshold voltage	$V_{GS(th)}$	-1.0			V	$I_D = -250\mu\text{A}$, $V_{DS}=V_{GS}$
Static Drain-Source on-state resistance (*)	$R_{DS(on)}$			0.080 0.140	Ω	$V_{GS} = -10\text{V}$, $I_D = -2.5\text{A}$ $V_{GS} = -4.5\text{V}$, $I_D = -1.9\text{A}$
Forward Transconductance (*) (†)	g_{fs}		5		S	$V_{DS} = -15\text{V}$, $I_D = -3\text{A}$
Dynamic (†)						
Input capacitance	C_{iss}		370		pF	$V_{DS} = -15\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output capacitance	C_{oss}		72		pF	
Reverse transfer capacitance	C_{rss}		38		pF	
Switching (‡) (†)						
Turn-on-delay time	$t_{d(on)}$		1.3		ns	$V_{DD} = -15\text{V}$, $V_{GS} = -10\text{V}$ $I_D = -1\text{A}$ $R_G \cong 6.0\Omega$,
Rise time	t_r		2.6		ns	
Turn-off delay time	$t_{d(off)}$		49		ns	
Fall time	t_f		22		ns	
Gate charge						
Total Gate charge	Q_g		7		nC	$V_{DS} = -15\text{V}$, $V_{GS} = -10\text{V}$ $I_D = -3\text{A}$
Gate-Source charge	Q_{gs}		1.2		nC	
Gate-Drain charge	Q_{gd}		1.3		nC	
Source-Drain diode						
Diode forward voltage (*)	V_{SD}		-0.80	-1.2	V	$I_S = -1.7\text{A}$, $V_{GS} = 0\text{V}$
Reverse recovery time (‡)	t_{rr}		14.6		ns	$I_S = -1.5\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge (‡)	Q_{rr}		9.5		nC	

NOTES:

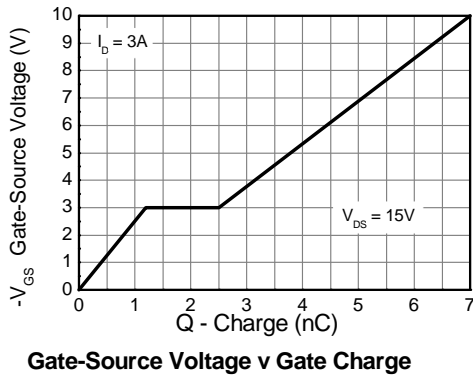
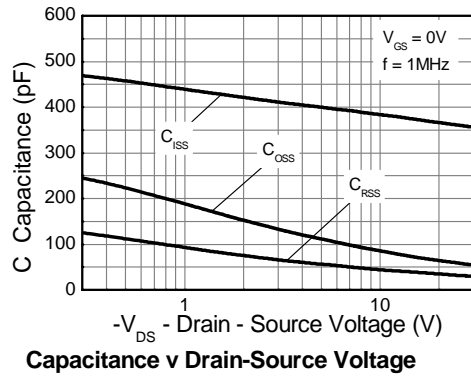
- (*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- (†) Switching characteristics are independent of operating junction temperature.
- (‡) For design aid only, not subject to production testing

Typical Characteristics

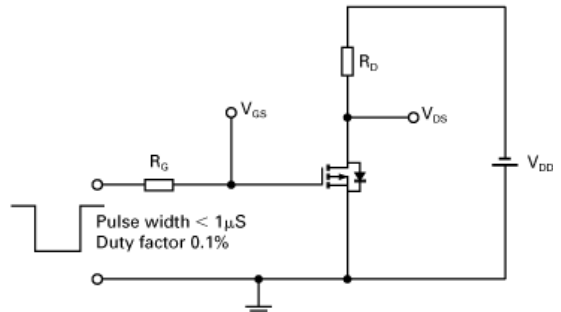
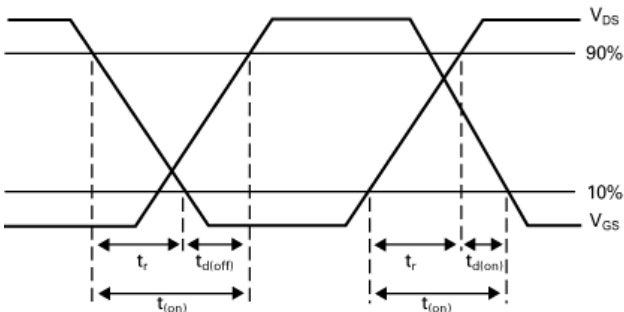
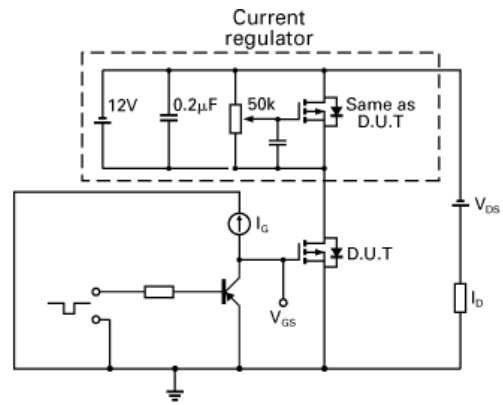
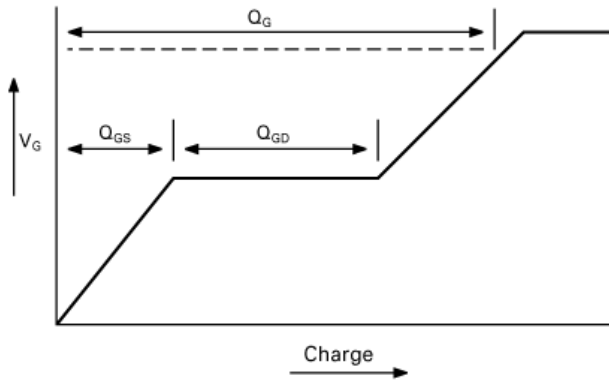


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Typical Characteristics

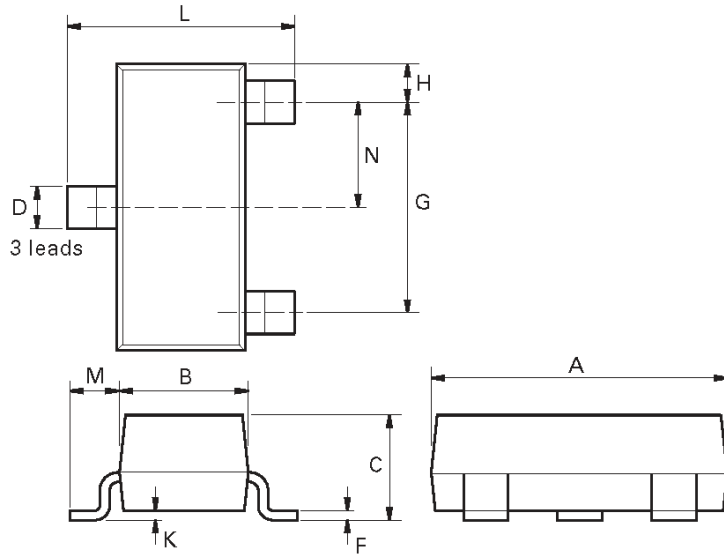


Test Circuits



Packaging Details – SOT23

Package outline



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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